



Diode Module

AMDD261N20K



Key Parameters

$I_{F(AV)M}$	=	260	A
V_{RRM}	=	2000	V
I_{FSM}	=	9500	A
V_{TO}	=	0.70	V
r_T	=	0.68	$m\Omega$

Properties

- International standard package
- High operation reliability
- Electrically insulated base plate

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters			Maximum Limits	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj} = -40^\circ C \dots T_{vj \max}$	2000	V
V_{RSM}	Non-repetitive peak reverse voltage	$T_{vj} = +25^\circ C \dots T_{vj \max}$	2100	V
I_{FAVM}	Average on-state current	$T_C = 100^\circ C$	260	A
I_{FRMSM}	Maximum RMS on-state current		410	A
I_{FSM}	Surge current	$T_{vj} = 25^\circ C, t_p = 10 \text{ ms}$ $T_{vj} = T_{vj \max}, t_p = 10 \text{ ms}$	9500 8300	A A
I^2t	Safety factor	$T_{vj} = 25^\circ C, t_p = 10 \text{ ms}$ $T_{vj} = T_{vj \max}, t_p = 10 \text{ ms}$	451000 344000	A^2s A^2s

CHARACTERISTICS

Symbols and parameters			Value			Unit
			min	typ	max	
V_F	On-state voltage	T _{vj} = T _{vj max} , I _F = 800 A			1.42	V
V_(TO)	Threshold voltage	T _{vj} = T _{vj max}			0.70	V
r_T	Slope resistance	T _{vj} = T _{vj max}			0.68	mΩ
I_R	Reverse current	T _{vj} = T _{vj max} , V _R = V _{RRM}			40	mA
V_{ISOL}	Insulation test voltage	RMS, f = 50Hz, t = 1 sec RMS, f = 50Hz, t = 1 min			3.6 3.0	kV

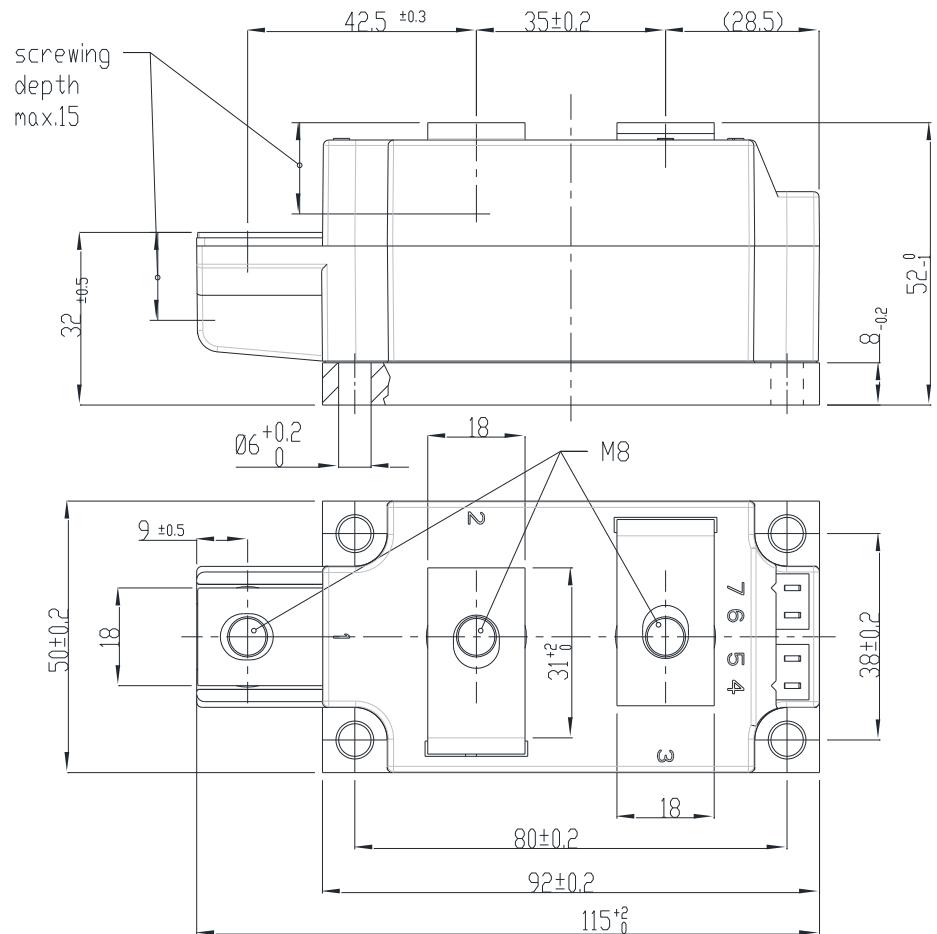
THERMAL PARAMETERS

Symbols and parameters			Value	Unit
R_{th(j-c)}	Thermal resistance, junction to case	per Module, θ = 180° sin per arm, θ = 180° sin per Module, DC per arm, DC	0.085 0.170 0.082 0.164	K/W
R_{th(c-h)}	Thermal resistance, case to heatsink	per Module per arm	0.02 0.04	K/W
T_{vj max}	Maximum junction temperature		+150	°C
T_{C op}	Operating temperature range		-40...+150	°C
T_{stg}	Storage temperature range		-40...+150	°C

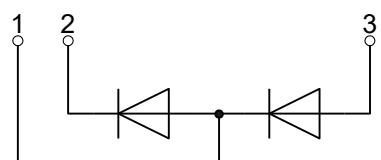
MECHANICAL PARAMETERS

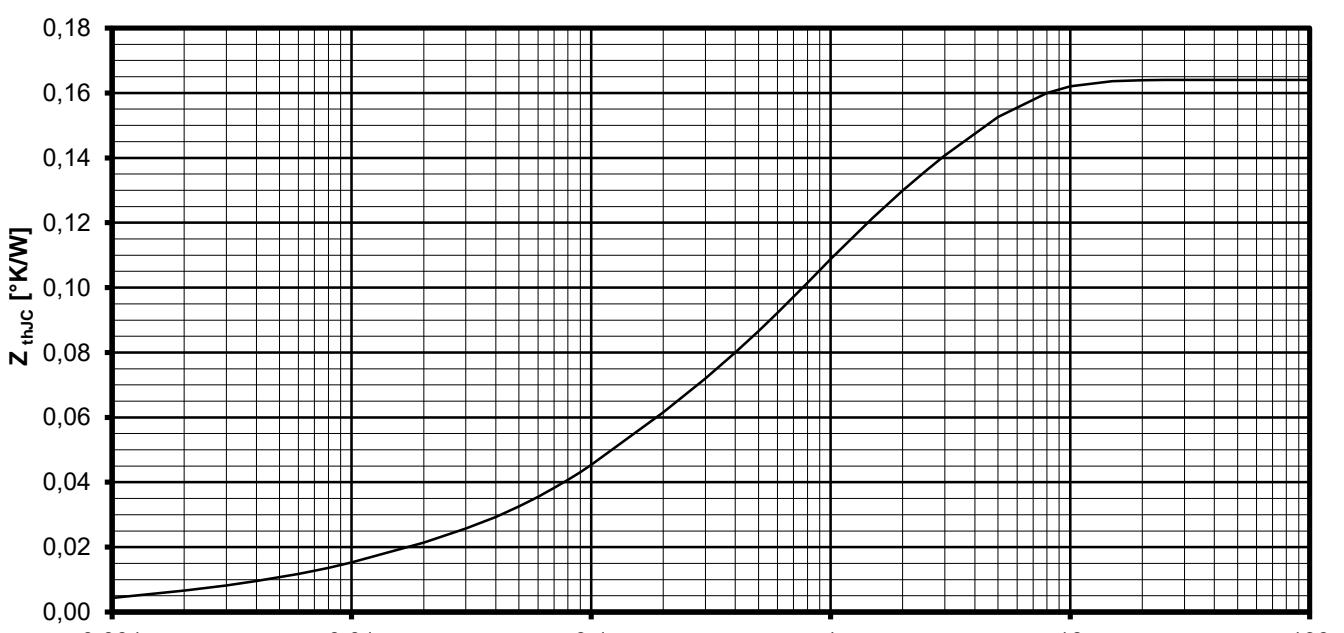
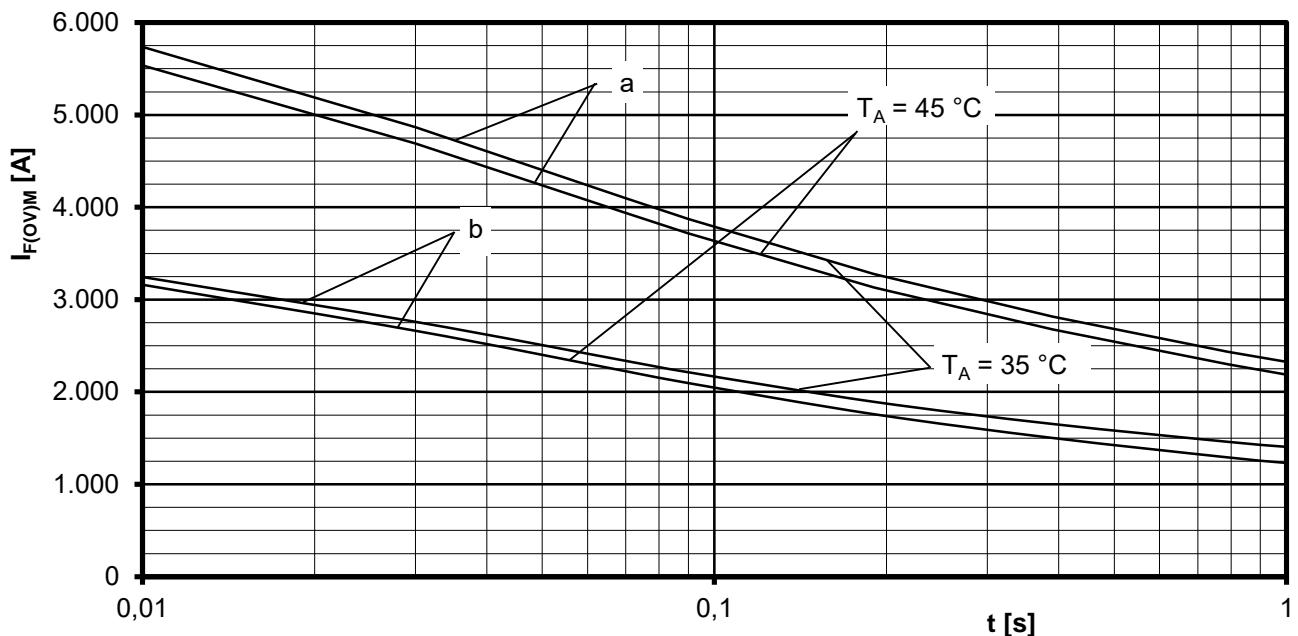
Symbols and parameters			Value	Unit
M1	Mounting torque	Tolerance ± 15%	6	Nm
M2	Terminal connection torque	Tolerance ± 10%	12	Nm
W	Weight		800	g
a	Vibration resistance	f = 50 Hz	50	m/s ²

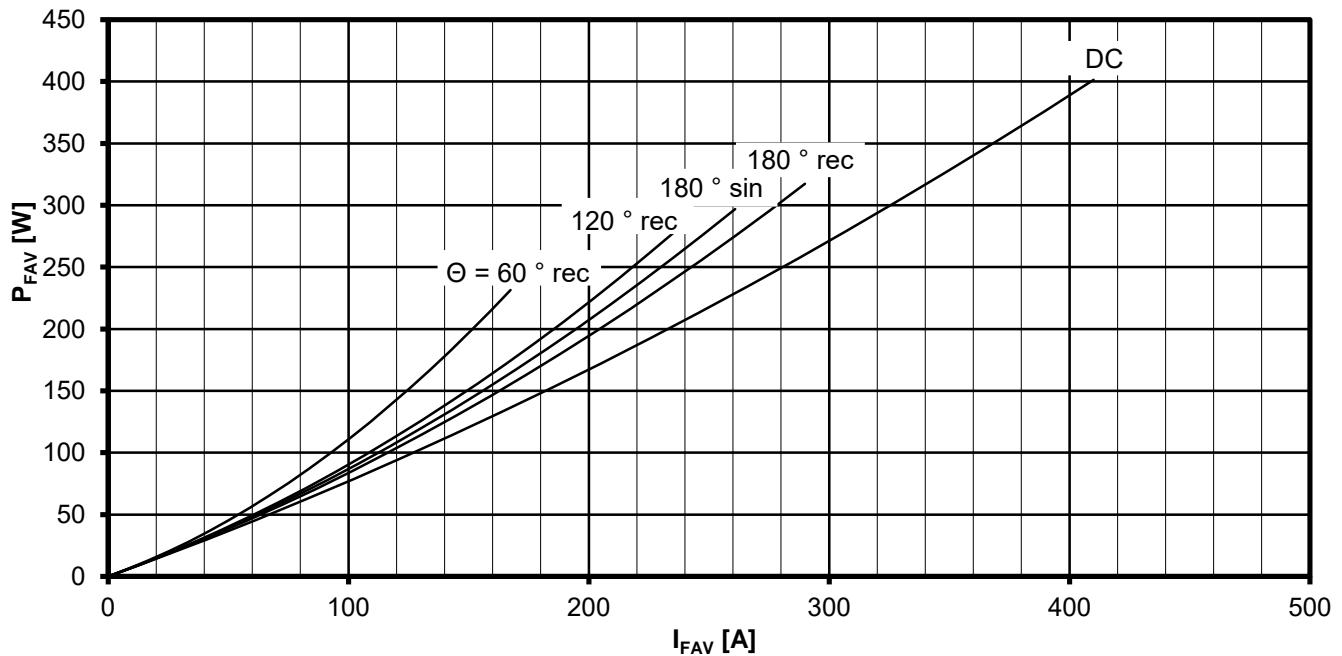
DIMENSIONS



TOPOLOGY OF INTERNAL CONNECTION

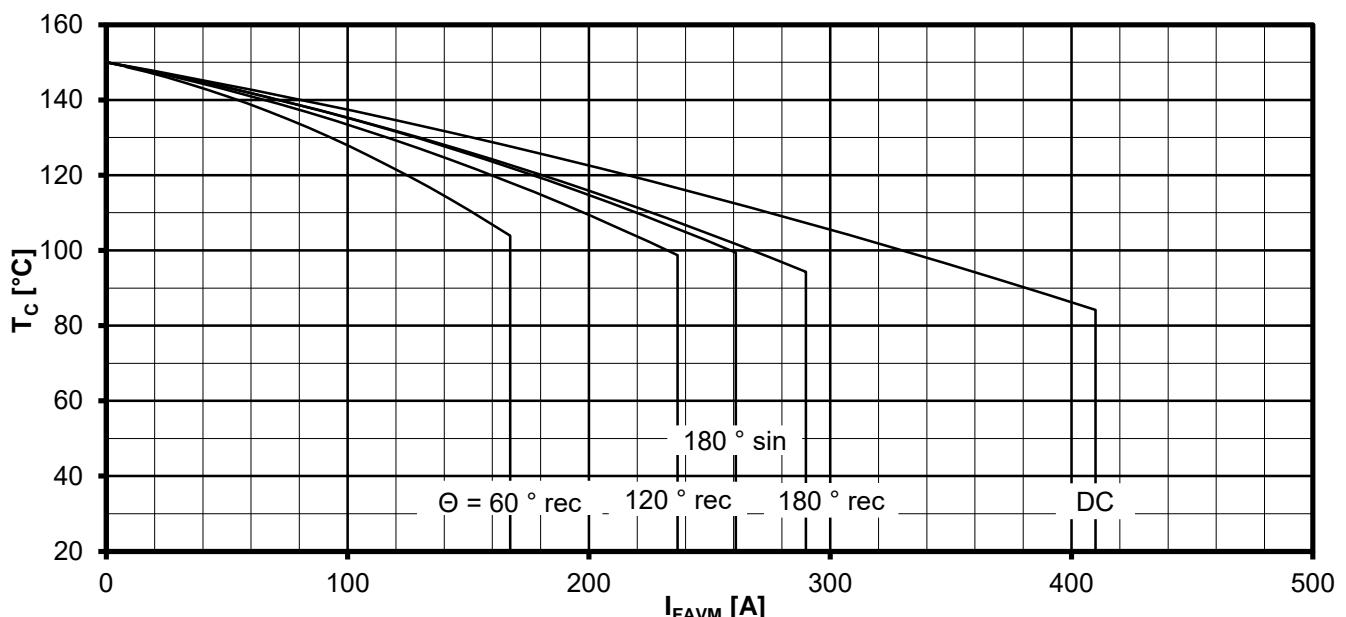






On-state power loss per arm $P_{FAV} = f(I_{FAV})$

Parameter: Current conduction angle Θ

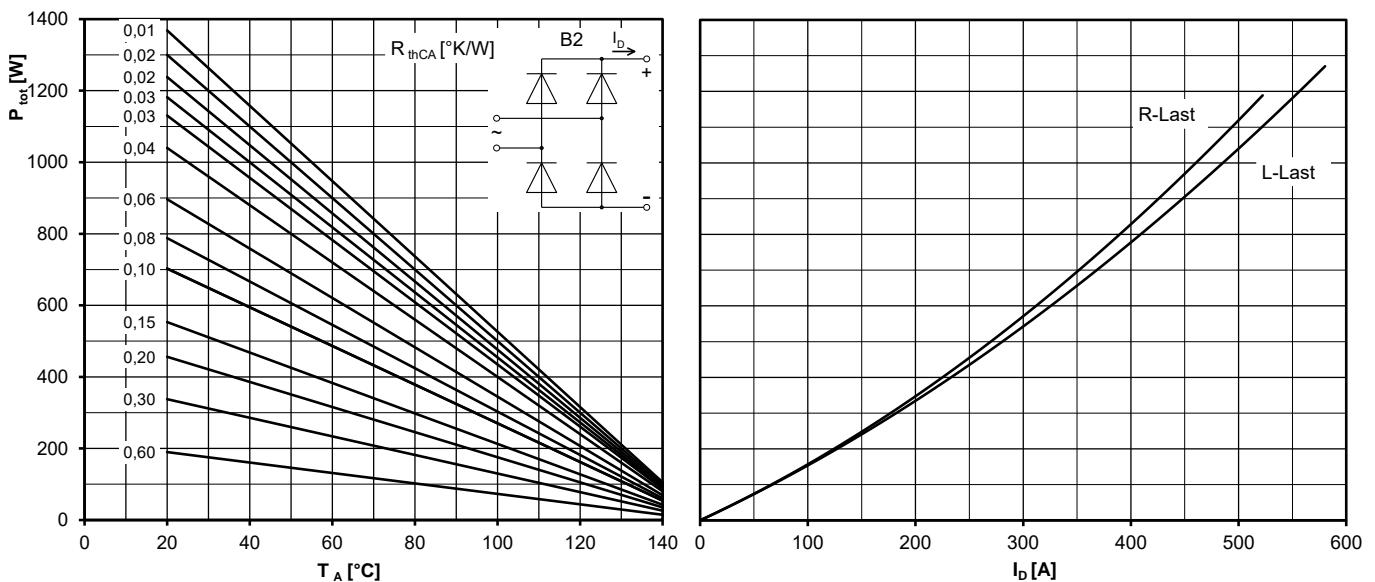


Maximum allowable case temperature $T_C = f(I_{FAVM})$

Current load per arm

Calculation base P_{TAV}

Parameter: Current conduction angle Θ



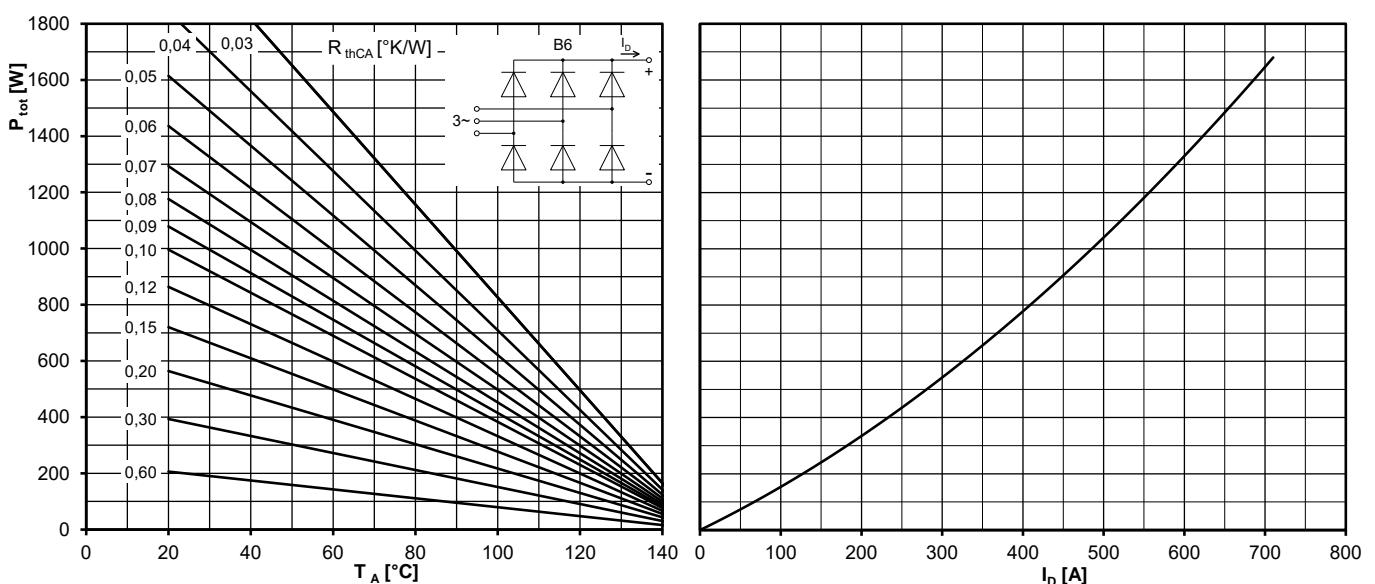
Maximum rated output current I_D

B2- Two-pulse bridge circuit

Total power dissipation at circuit P_{tot}

Parameter:

Thermal resistance cases to ambient R_{thCA}



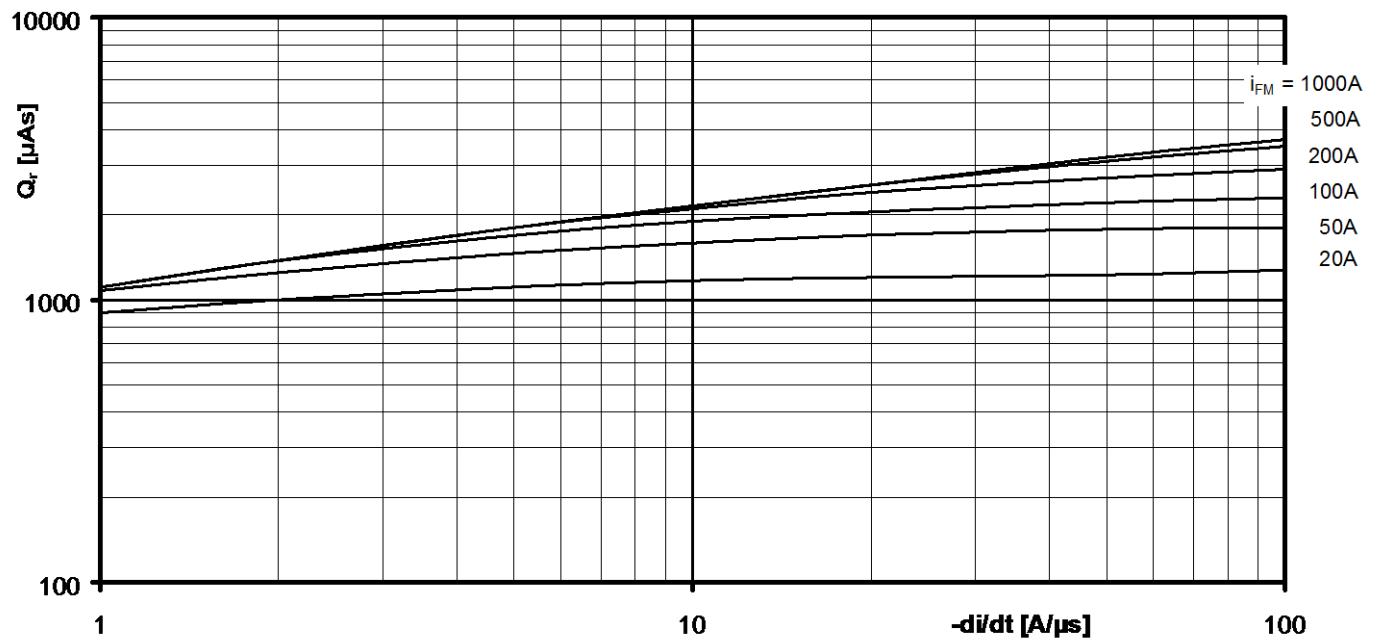
Maximum rated output current I_D

B6- Six-pulse bridge circuit

Total power dissipation at circuit P_{tot}

Parameter:

Thermal resistance cases to ambient R_{thCA}



Recovered charge $Q_r = f(-di/dt)$

$T_{vj} = T_{vjmax}$, $v_R \leq 0,5 V_{RRM}$, $v_{RM} = 0,8 V_{RRM}$

Parameter: On-state current i_{FM}